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## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

DEC 02 2005

Applicants: Bao, *et al.* Docket No.: TSM03-0927  
Serial No.: 10/800,510 Art Unit: 2818  
Filed: March 15, 2004 Examiner: Tu-Tu Ho  
For: Semiconductor Device Having a Second Level of Metallization Formed  
over a First Level with Minimal Damage to the First Level and Method

Mail Stop: Amendment  
Commissioner for Patents  
P. O. Box 1450  
Alexandria, VA 22313-1450

AMENDMENT

Dear Sir:

The following amendments and remarks are presented in response to the Examiner's Office Action mailed August 3, 2005. Please amend the above-referenced application as follows.

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Amendment

PAGE 4/14 \* RCVD AT 12/2/2005 2:14:48 PM [Eastern Standard Time] \* SVR:USPTO-EFXRF-6/37 \* DNIS:2738300 \* CSID:9727329218 \* DURATION (mm:ss):03:02